

RJK5014DPK

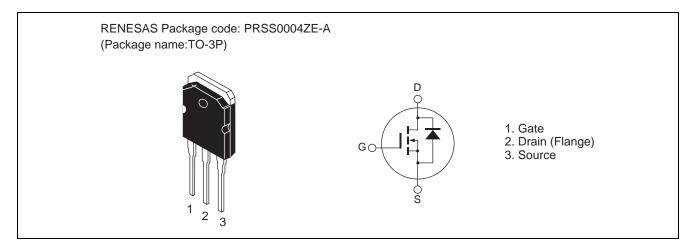
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1458-0200 Rev.2.00 Oct 20, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit | |
|---|-------------------------------|-------------|------|--|
| Drain to source voltage | V _{DSS} | 500 | V | |
| Gate to source voltage | V_{GSS} | ±30 | V | |
| Drain current | I _D | 19 | A | |
| Drain peak current | I _{D (pulse)} Note1 | 38 | Α | |
| Body-drain diode reverse drain current | I _{DR} | 19 | Α | |
| Body-drain diode reverse drain peak current | I _{DR (pulse)} Note1 | 38 | Α | |
| Avalanche current | I _{AP} Note3 | 5 | Α | |
| Avalanche energy | E _{AR} Note3 | 1.3 | mJ | |
| Channel dissipation | Pch Note2 | 150 | W | |
| Channel to case thermal impedance | θch-c | 0.833 | °C/W | |
| Channel temperature | Tch | 150 | °C | |
| Storage temperature | Tstg | −55 to +150 | °C | |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

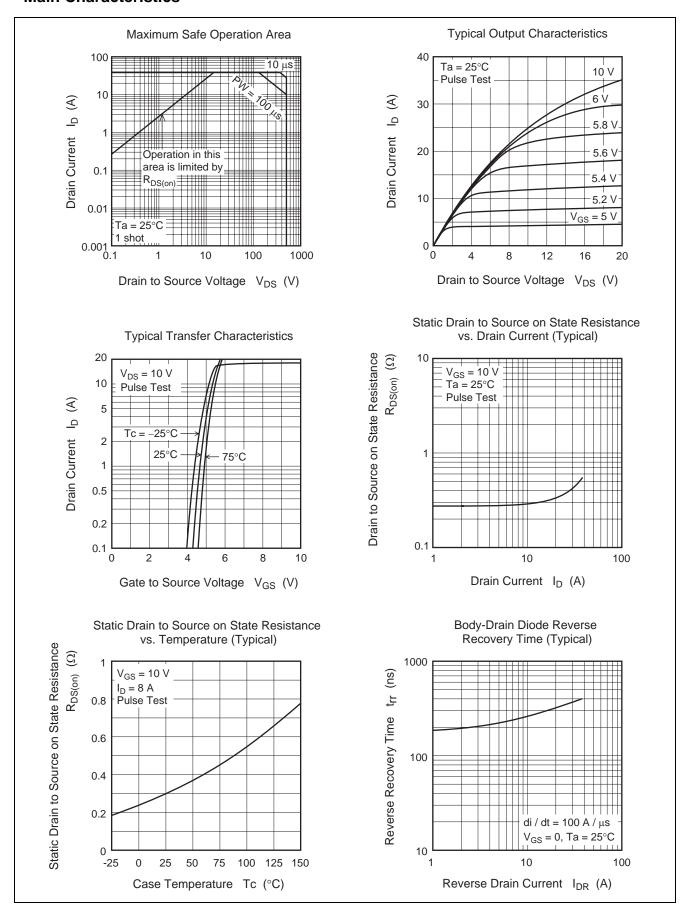
Electrical Characteristics

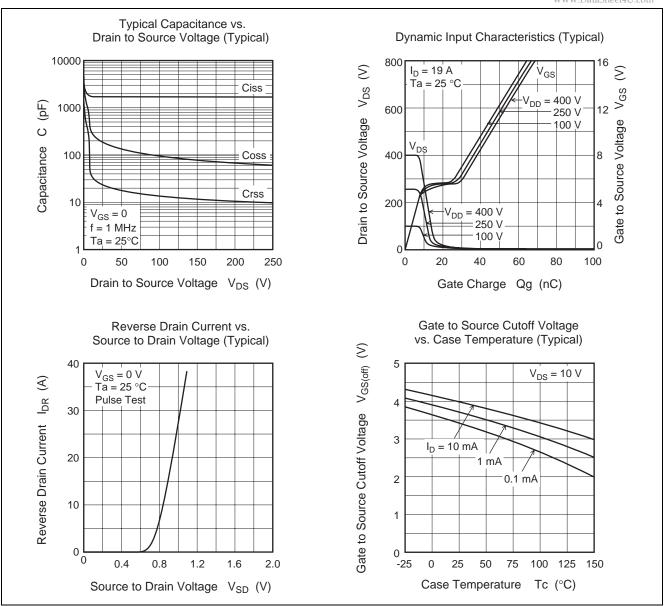
 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--|----------------------|-----|-------|-------|------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 500 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 500 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±0.1 | μΑ | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$ |
| Gate to source cutoff voltage | V _{GS(off)} | 3.0 | _ | 4.5 | V | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 0.315 | 0.380 | Ω | $I_D = 9.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$ |
| Input capacitance | Ciss | _ | 1800 | _ | pF | V _{DS} = 25 V |
| Output capacitance | Coss | _ | 190 | _ | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 24 | _ | pF | f = 1 MHz |
| Turn-on delay time | t _{d(on)} | _ | 36 | _ | ns | I _D = 9.5 A |
| Rise time | t _r | _ | 41 | _ | ns | V _{GS} = 10 V |
| Turn-off delay time | t _{d(off)} | _ | 93 | _ | ns | $R_L = 26.3 \Omega$ |
| Fall time | t _f | _ | 39 | _ | ns | $Rg = 10 \Omega$ |
| Total gate charge | Qg | _ | 46 | _ | nC | V _{DD} = 400 V |
| Gate to source charge | Qgs | _ | 9 | _ | nC | V _{GS} = 10 V |
| Gate to drain charge | Qgd | _ | 20 | _ | nC | I _D = 19 A |
| Body-drain diode forward voltage | V_{DF} | _ | 0.91 | 1.55 | V | $I_F = 19 \text{ A}, V_{GS} = 0^{\text{Note4}}$ |
| Body-drain diode reverse recovery time | t _{rr} | _ | 320 | _ | ns | $I_F = 19 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

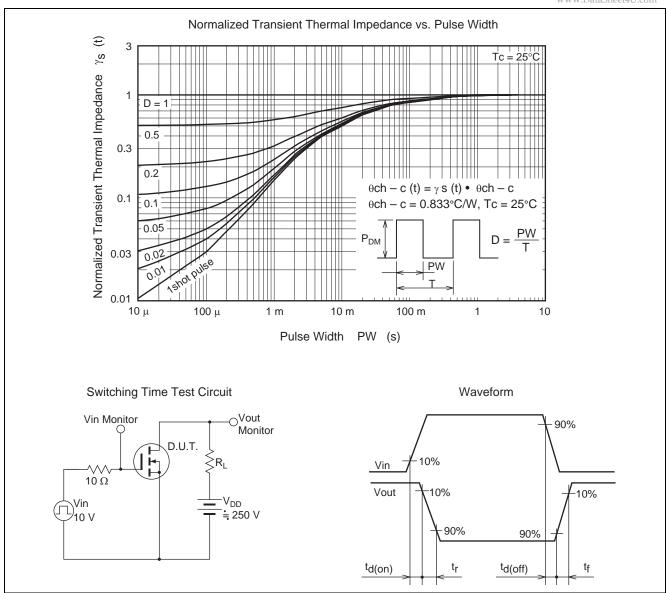
Notes: 4. Pulse test

Main Characteristics

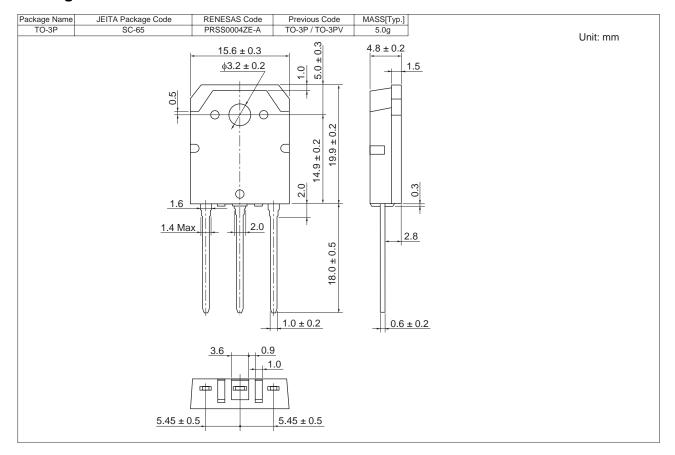




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Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK5014DPK-00-T0 | 360 pcs | Box (Tube) |

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